



DMTH4007SPSQ

POWERDI

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C (Note 10)
40V	7.6mΩ @ V _{GS} = 10V	100A

Description and Applications

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Power Management
- DC-DC Converters
- Motor Control

Features

 Rated to +175°C – Ideal for High Ambient Temperature Environments

40V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET

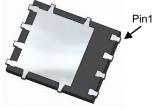
- Thermally Efficient Package-Cooler Running Applications
- High Conversion Efficiency
- Low R_{DS(ON)} Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- <1.1mm Package Profile Ideal for Thin Applications</p>
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

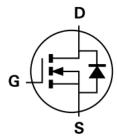
- Case: POWERDI[®]5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.097 grams (Approximate)



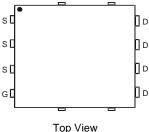
Top View



Bottom View



Internal Schematic



Top View Pin Configuration

Ordering Information (Note 5)

Part Number	Case	Packaging	
DMTH4007SPSQ-13	POWERDI [®] 5060-8	2,500 / Tape & Reel	

POWERDI[®]5060-8

Notes: 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

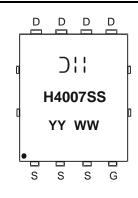
4. Automotive products are AEC-Q101 qualified and are PPAP capable. For more information, please refer to

http://www.diodes.com/product_compliance_definitions.html.

5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.



Marking Information



) | | = Manufacturer's Marking H4007SS = Product Type Marking Code YYWW = Date Code Marking YY = Last Digit of Year (ex: 14 = 2014) WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Drain-Source Voltage		V _{DSS}	40	V
Gate-Source Voltage		V _{GSS}	±20	V
Continuous Drain Current (Note 6)	T _A = +25°C T _A = +70°C	ID	15.7 13.1	А
Continuous Drain Current (Note 7)	$T_{C} = +25^{\circ}C$ (Note 10) $T_{C} = +100^{\circ}C$	ID	100 77	А
Maximum Continuous Body Diode Forward Current (Note	7)	Is	100	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		IDM	120	А
Avalanche Current, L=0.3mH		I _{AS}	20	А
Avalanche Energy, L=0.3mH		E _{AS}	60	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 6)	$T_A = +25^{\circ}C$	PD	2.8	W
Thermal Resistance, Junction to Ambient (Note 6)		R _{0JA}	53	°C/W
Total Power Dissipation (Note 7)	$T_{C} = +25^{\circ}C$	PD	136	W
Thermal Resistance, Junction to Case (Note 7)		R _{eJC}	1.1	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +175	°C

 Notes:
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.

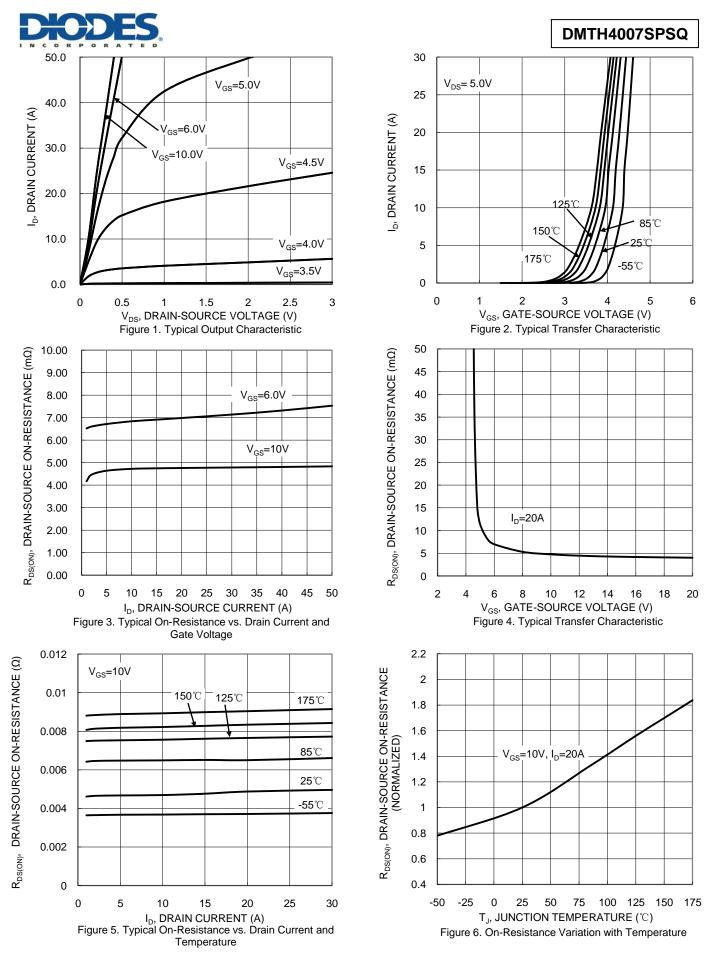
 7. Thermal resistance from junction to soldering point (on the exposed drain pad).



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)								
Drain-Source Breakdown Voltage		BV _{DSS}	40		_	V	$V_{GS} = 0V, I_D = 1mA$	
Zere Cate Malte as Drain Current	-	I _{DSS}	—		1	μA	$V_{DS} = 32V, V_{GS} = 0V$	
Zero Gate Voltage Drain Current	(Note 9)	IDSS			100	μA	$V_{DS} = 32V, V_{GS} = 0V, T_J = +125^{\circ}C$	
Gate-Source Leakage		I _{GSS}	—		±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)								
Gate Threshold Voltage		V _{GS(TH)}	2	l	4	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance		R _{DS(ON)}	—	4.9	7.6	mΩ	$V_{GS} = 10V, I_D = 20A$	
Diode Forward Voltage		V _{SD}		_	1.2	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 9)								
Input Capacitance		Ciss	—	2,082	—			
Output Capacitance Reverse Transfer Capacitance		Coss	—	790	—	pF	$V_{DS} = 25V, V_{GS} = 0V,$ f = 1MHz	
		Crss		113	_			
Gate Resistance		Rg	0.1	0.46	1.4	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge	Total Gate Charge		_	41.9				
Gate-Source Charge		Q _{gs}		10	_	nC	V _{DS} = 30V, I _D = 20A, V _{GS} = 10V	
Gate-Drain Charge		Q _{gd}	_	11.5				
Turn-On Delay Time		t _{D(ON)}		7				
Turn-On Rise Time		t _R	_	11.5			$\label{eq:VDD} \begin{split} V_{DD} &= 30V, \ V_{GS} = 10V, \\ I_D &= 20A, \ R_G = 3\Omega \end{split}$	
Turn-Off Delay Time		t _{D(OFF)}		15.6	—			
Turn-Off Fall Time		tF		8.8	—			
Body Diode Reverse Recovery Time		t _{RR}		29.9	—	ns		
Body Diode Reverse Recovery Charge		Q _{RR}		23		nC	I _F = 20A, di/dt = 100A/μs	

8. Short duration pulse test used to minimize self-heating effect. Notes: Guaranteed by design. Not subject to product testing.
 Package limited.

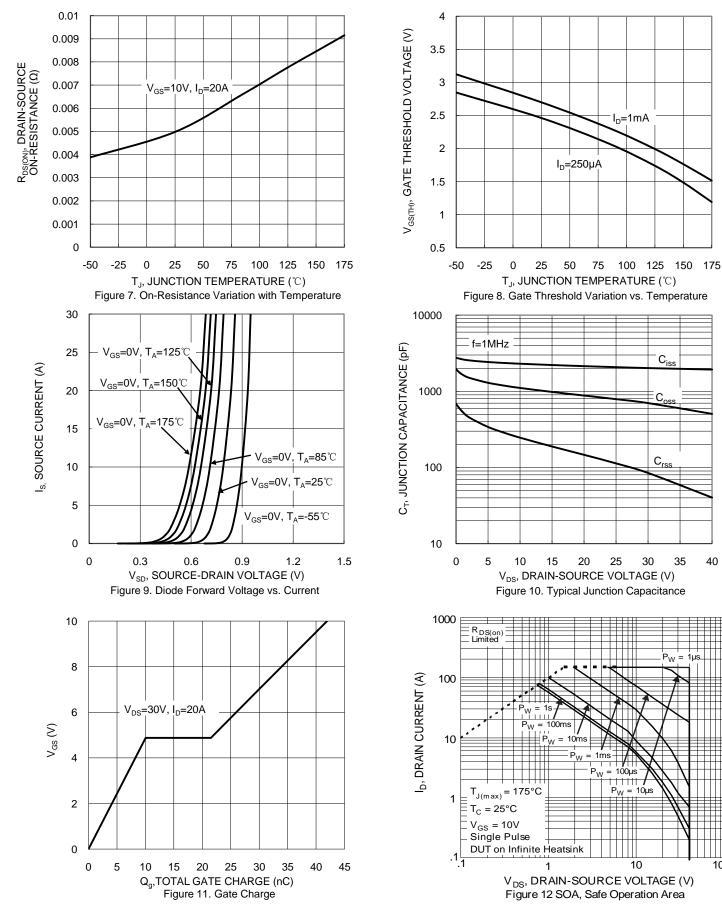


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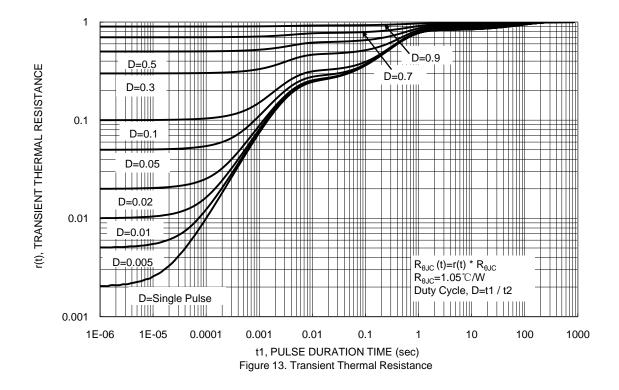


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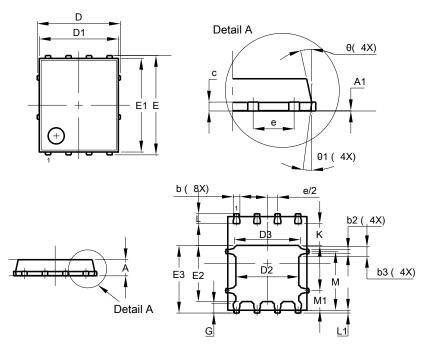




Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

POWERDI[®]5060-8

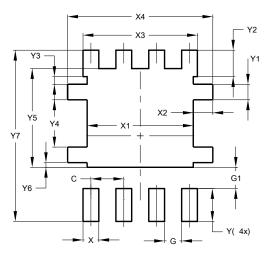


POWERDI [®] 5060-8						
Dim	Min	Max	Тур			
Α	0.90	1.10	1.00			
A1	0.00	0.05	_			
b	0.33	0.51	0.41			
b2	0.200	0.350	0.273			
b3	0.40	0.80	0.60			
С	0.230	0.330	0.277			
D		5.15 BSC				
D1	4.70	5.10	4.90			
D2	3.70	4.10	3.90			
D3	3.90	4.30	4.10			
ш	(6.15 BSC				
E1	5.60	6.00	5.80			
E2	3.28	3.68	3.48			
E3	3.99	4.39	4.19			
е		1.27 BSC				
G	0.51	0.71	0.61			
K	0.51		—			
L	0.51	0.71	0.61			
L1	0.100	0.200	0.175			
М	3.235	4.035	3.635			
M1	1.00	1.40	1.21			
θ	10°	12°	11°			
θ1	6°	8°	7°			
All Dimensions in mm						

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

POWERDI[®]5060-8



Dimensions	Value (in mm)
С	1.270
G	0.660
G1	0.820
Х	0.610
X1	4.100
X2	0.755
X3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610



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